Habib Ahmad

List of Publications by Year
in descending order

17 papers	195 citations	1163117 8 h-index	1125743 13 g-index
18 all docs	18 docs citations	18 times ranked	197 citing authors

#	Article	IF	Citations
1	Wet-based digital etching on GaN and AlGaN. Applied Physics Letters, 2022, 120, .	3.3	4
2	GaN:Be I-Layer-Based High-Power p-i-n Diodes Achieving Large Quasi-Vertical MBE Breakdown Performance. IEEE Transactions on Electron Devices, 2022, , 1-7.	3.0	0
3	Realization of homojunction PN AlN diodes. Journal of Applied Physics, 2022, 131, .	2.5	16
4	Stable and High Performance AlGaN Self-Aligned-Gate Field Emitter Arrays. IEEE Electron Device Letters, 2022, 43, 1351-1354.	3.9	8
5	Upper limits to thermal conductance across gallium nitride interfaces: Predictions and measurements. , 2022, , 83-102.		0
6	Thermal conductivity measurements of sub-surface buried substrates by steady-state thermoreflectance. Review of Scientific Instruments, 2021, 92, 064906.	1.3	17
7	Substantial Pâ€Type Conductivity of AlN Achieved via Beryllium Doping. Advanced Materials, 2021, 33, e2104497.	21.0	33
8	High thermal conductivity and thermal boundary conductance of homoepitaxially grown gallium nitride (GaN) thin films. Physical Review Materials, 2021, 5, .	2.4	10
9	Adlayer control for tunable AlGaN self-assembled superlattices. Journal of Applied Physics, 2021, 130, .	2.5	5
10	p-type AlN based heteroepitaxial diodes with Schottky, Pin, and junction barrier Schottky character achieving significant breakdown performance. Journal of Applied Physics, 2021, 130, 195702.	2.5	3
11	Thermal conductance across harmonic-matched epitaxial Al-sapphire heterointerfaces. Communications Physics, 2020, 3, .	5.3	41
12	Comprehensive Analysis of Metal Modulated Epitaxial GaN. ACS Applied Materials & Interfaces, 2020, 12, 37693-37712.	8.0	15
13	Thermal boundary conductance across epitaxial metal/sapphire interfaces. Physical Review B, 2020, 102, .	3.2	26
14	Beryllium doped semi-insulating GaN without surface accumulation for homoepitaxial high power devices. Journal of Applied Physics, 2020, 127, 215703.	2.5	13
15	TCAD design of InGaN-based monolithic multi-wavelength LED with controlled Power spectral distributions. Optik, 2015, 126, 3140-3144.	2.9	1
16	Design of a Monolithic Dual Emission InGaN Based White Light-Emitting Diode. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 338-347.	0.5	0
17	Cascaded Ni hard mask to create chlorine-based ICP dry etched deep mesas for high-power devices. Semiconductor Science and Technology, 0, , .	2.0	3